

a second semiconductor chip and a third semiconductor chip installed on a support substrate, wherein said second semiconductor chip and said third semiconductor chip are connected with each other through said first semiconductor chip; and

wherein said <sup>first</sup> semiconductor chip is a DRAM chip, and said third semiconductor chip is a logic chip.

4. (Amended) [The semiconductor device according to claim 3, wherein] A semiconductor device comprising:

a semiconductor chip consisting of at least either a circuit against static damage or a passive component, wherein said semiconductor chip consists of only said passive component, said passive component includes all of a resistor, a capacitor and a reactor.

5. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (Amended) [The] A semiconductor device [according to claim 8,] comprising:

a plurality of semiconductor chips installed on a support substrate; [and]  
a wire connecting said plurality of semiconductor chips with each other and  
having a passive component function; and

wherein said wire having a passive component function has a length greater than that for linearly connecting terminals of said plurality of semiconductor chips with each other thereby forming a resistive element.